

Origin of the Curie-von Schweidler law and the fractional capacitor from time-varying capacitance

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Abstract

Most dielectrics of practical purpose exhibit memory and are described by the century old Curie-von Schweidler law. Interestingly, the Curie-von Schweidler law is the motivation behind an unconventional circuit component called *fractional capacitor* which due to its power-law properties is extensively used in the modeling of complex dielectric media. However, the empirical nature of the Curie-von Schweidler law also plagues the use of the fractional capacitor. Here, we derive the Curie-von Schweidler law from a series combination of a resistor and a capacitor with a linearly time-varying capacitance. This may possibly be its first derivation from physical principles. However, this required a modification of the traditional charge-voltage relation of a capacitor to account for the time-varying capacitance. The limitation of the classical charge-voltage relation and its modification are justified with suitable arguments. Consequently, the parameters of the Curie-von Schweidler law and the fractional capacitor gain physical interpretation. The Debye response of dielectrics is shown to emerge naturally from the limiting case of the power-law response at short time scales. The obtained results are validated by matching them with the published experimental reports.

Keywords: Curie-von Schweidler law, universal dielectric response, fractional capacitor, fractional calculus, power-laws, memory

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1. Introduction

Most electrical appliances of daily use contain capacitors to store electrical energy. The storage of energy occurs through charge accumulation on the capacitor plates. This is facilitated by the dielectric media in the capacitor that exhibits high polarizability under the action of an applied electrical field. However, a lag in the polarization leads to a dielectric relaxation. Since an insight into the optical and electrical properties of a dielectric is possible from its relaxation behavior, the study of dielectric relaxation has attracted interest from material scientists and electrical engineers alike for more than a century [1].

According to the classical theory of Debye relaxation, the current response, $I_D(t)$, of an *ideal* dielectric to an input step voltage is a memory-less exponential decay, i.e., $I_D(t) \propto \exp(-t/\tau_D)$, where, t is the time, and τ_D is the Debye relaxation time constant. The response constitutes sum of responses from non-interacting population of dipoles however that could only be justified for relatively dilute dipolar systems in which the inter-particle distances are large. In contrast, most dielectrics are solids and so mutual interactions cannot be ignored. Solid dielectrics exhibit memory, i.e., they remember their past excitations because of non-Debye relaxation mechanisms. Such a memory-laden behavior is often described using power-laws [2] which was first experimentally inferred by Curie in 1889 [3] and later rediscovered by von Schweidler in 1907 [4]. The Curie-von Schweidler (CvS) law describes the power-law decay of a depolarizing current in a dielectric that is subjected to a step DC voltage as:

$$I(t) = a \left(\frac{t}{\tau} \right)^{-\alpha}, \quad (1)$$

where a has the dimension of current, τ is the characteristic relaxation time constant, and $0 < \alpha < 1$ is the decay constant. Some other equations have also been proposed to describe dielectric relaxation, such as Cole-Cole [5], Cole-Davidson [6], Havriliak-Negami [7], and Kohlrausch-Williams-Watts [8, 9], but in comparison to Eq. (1), other empirical equations are relatively difficult to

curve-fit [10]. Consequently, the CvS law arguably remains the preferred one among all. Also, the CvS law is weakly influenced by the physical structure, geometric configurations, and chemical bonding of the material. Besides, it is largely independent of the nature of the polarizing species, be they hopping electrons, ions, or dipoles [2]. The law holds regardless of changes in temperature except when the change is radical. Since the CvS law is sufficiently good and surprisingly better in most cases, it was declared as the universal dielectric response (UDR) [1, 2]. Further, the Fourier transform property of the power-law, $\mathcal{F}[t^{-\alpha}] = \Gamma(1 - \alpha)(i\omega)^{\alpha-1}$, for $t > 0$, is used to alternatively express the CvS law as, $\chi(\omega) \propto \omega^{\alpha-1}$, where χ is the complex electric susceptibility, ω is the angular frequency, and $\Gamma(\cdot)$ is the Euler Gamma function [2]. The validity of the relation is established in as many as eight to ten decades of frequency [1, 11, 12]. It is worthwhile to mention that the CvS law is plagued by a mathematical singularity at extremely short time-scales which also mirrors at very high ($> \text{THz}$) frequencies. The underlying physical reason behind this nature is the dominating quantum effects due to phonon and lattice vibrations [1]. In the remaining part of this manuscript we focus on the CvS law expressed by Eq. (1) for two reasons; first, because of its historical context, and second, because it is relatively easier to measure current than susceptibility in experiments.

Probably, the first attempt to uncover the physics underlying the CvS law was motivated from a pure mathematical result that equals power law with an infinite weighted sum of Debye relaxation responses [4]. Since the respective circuit model consists of an infinite ladder network of resistors and capacitors [13], it leads to an infinite system of first order differential equations. The each of those differential equations yields a weighted exponential with a distinct relaxation time constant as its solution [1]. However, irrespective of the mathematical consistency, the breadth and form of any such relaxation distribution is difficult to comprehend [14, 15]. Since they neither aid nor advance the understanding, the reasoning is arbitrary and may even be considered superfluous [2, 5]. Even though von Schweidler had followed the same approach [4], it is seen as a mere attempt to reconcile the observed memory exhibits with the desired yet

incompatible memory-less Debye relaxation processes. This is understandable because back then it was almost counter-intuitive to acknowledge that matter could have memory.

An alternative mechanism is many body interactions that manifests from the nonlocal reciprocal interactions between the polarizing species and the matter lattice in which they move [2, 11], but it is impossible to study them at atomic and molecular levels because of the resulting mathematical complexities [1, 16]. Also, the values of the density and the magnitude of the polarizing species are rarely available [17]. Some more attempts inspired from the common observation of self-similarity in power-laws and fractal geometry have been made [18–22]. Unfortunately, those attempts and a few others [23, 24] are all specifically tailored to satisfy the observed power-law behavior without giving any insight into the mechanism that governs the UDR. This is evident from the lack of a physical interpretation of the parameters, a , τ , and α . Unfortunately, the status of the UDR has reduced to an empirical relation that can only be used to curve-fit the experimental data [25–29].

The undeniable fact that the CvS law is ubiquitous indicates that a more fundamental yet a universal mechanism is at play. In fact, its theoretical description is considered as one of most *fundamental* problems in physics [11, 17, 30–32]. Therefore, the quest for an encompassing interpretation becomes imperative and serves as a motivation for this manuscript. Coincidentally, the power-law anchored in Eq. (1) is inherent in the definition of a fractional derivative. The Caputo definition for the fractional derivative of a causal, continuous function, $f(x)$, is the convolution of an integer-order derivative with a power-law memory kernel, $\phi_\alpha(t)$, as [33]:

$$\frac{d^\alpha}{dt^\alpha} f(t) \stackrel{\text{def.}}{=} \dot{f}(t) * \phi_\alpha(t), \quad \phi_\alpha(t) = \frac{t^{-\alpha}}{\Gamma(1-\alpha)}, \quad 0 < \alpha < 1, \quad (2)$$

where the number of over-dots represent the order of differentiation with respect to time, t . Although fractional derivatives are expressed in the integro-differentiable form, their Fourier transform property, $\mathcal{F}[d^\alpha f(t)/dt^\alpha] = (i\omega)^\alpha \mathbf{f}(\omega)$, affirm that they are a mere generalization of the regular integer-order deriva-

tives. For negative values of α , Eq. (2) corresponds to a fractional integral.

The motivation to investigate the UDR using fractional derivatives is threefold. *First*, the kernel, $\phi_\alpha(t)$, from Eq. (2) is identified as the power law that characterizes the CvS law described by Eq. (1). In addition, since $\mathcal{F}[\phi_\alpha(t)]$ yields the respective UDR in the frequency domain, fractional derivatives appear as a natural tool for their investigation [31, 34]. Further it is known that the evolution of macroscopic memory from the underlying microscopic mechanisms is very complex and so fractional derivatives are almost inevitable [35]. It should be noted that fractional derivatives inherently include a multiscale generalization that accounts for the nonlocal interactions [36, 37]. Interestingly, Westerlund had even claimed that Nature works with fractional derivatives [38].

Second, electrical engineers have exploited the universality of the UDR in the modeling of biological membranes [39–41], differentiation of cancerous tissues from healthier tissues [42], and designing of new energy storage devices, example supercapacitors [25, 43, 44]. The respective circuit models often include an unconventional component called fractional capacitor whose current-voltage relation is [43]:

$$I_{C_f}(t) = C_f \frac{d^\alpha V_{C_f}(t)}{dt^\alpha}, \quad C_f = G\tau^\alpha, \quad (3)$$

where $I_{C_f}(t)$ and $V_{C_f}(t)$ are the current and the voltage, C_f is the pseudocapacitance, $G = 1/R$, is the electrical conductance, R represents the inherent resistance, and τ is the same as in Eq. (1). Since for $0 < \alpha < 1$, a fractional capacitor exhibits an interplay between a resistance and a capacitor, it may be seen as an electrical analogue of a fractional dashpot from non-Newtonian rheology [45]. In light of Eq. (2), the memory kernel rooted in Eq. (3) is inferred to be the CvS law. The fractional capacitor has a characteristic frequency-independent fixed phase angle, $|\alpha\pi/2|$, which means the energy lost per cycle is the same fraction of the energy stored at all frequencies. This is the same as the constant ratio of, $\Im[\chi(\omega)]/\Re[\chi(\omega)]$, where \Re and \Im denote the real and imaginary parts of a complex number. For these reasons, the fractional capacitor is also called the *constant phase element*. Although Jonscher had already claimed the CvS

law to be the response of a “universal” capacitor [1, p. 87], Westerlund formally introduced the same as a fractional capacitor to the electrical engineers community [38, 46]. Interestingly, the first affirmation regarding the universality of the CvS law can be traced back to the Cole-brothers who were probably motivated from Gemant’s work on rheology [47] whom they even cited as Ref. [42] in their work [5]. The versatility of fractional capacitor leads to the requirement of fewer parameters in the modeling of complex electrical behavior. Their use provides a better curve-fit than those from integer-order derivatives, but they suffer from an inherent drawback that arises from the lack of a physical interpretation of the fractional-order [48, 49].

Third, power-law behaviors are common in acoustics too and their investigation using fractional derivatives has led to the development of the field of fractional viscoelasticity [33, 50]. Similar to the case of the dielectric modeling, the application of fractional derivatives in rheological modeling usually had their motivation from the continuum of multiple relaxation processes [51]. However, some recent works have derived fractional differential equations from physical principles that have also led to the physical interpretation of the fractional order [45, 52–56]. Some of those findings [45] have also been independently verified in experiments [57–59].

The rest of the article is organized as follows. Sec. 2 is divided into two subsections. In its first subsection, we first prove the limitation of the classical charge-voltage relation for a time-varying capacitor. In particular, it is shown that the classical relation, $Q(t) = CV(t)$, that relates the charge, Q , with the capacitance, C , and the voltage, V , is not applicable for capacitors with a time-varying capacitance, $C(t)$. The expression for the current, dQ/dt , that is subsequently obtained following the substitution of C by $C(t)$ in the classical relation corresponds to an inconsistent circuit. The inconsistency of the circuit is resolved in the second subsection of Sec. 2 where a modified charge-voltage relation is proposed and suitably justified. The modified charge-voltage relation is then used to derive the universal dielectric response, the CvS law, in Sec. 3. Lastly in Sec. 4 the implications of this work is discussed.

2. Revision of classical charge-voltage relation

An efficient way to represent a capacitor's memory is to assume a time-varying capacitance, $C(t)$. Such an assumption has been used in the study of, solid state devices [60, 61], time-varying storage components [62, 63], energy accumulation [64], brain microvasculature [65], and biomimetic membranes [66]. Most of these cited references refer to the following charge-voltage equation,

$$Q(t) = C(t)V(t), \quad (4)$$

as a starting point in their studies. The equation is directly motivated from the classical charge-voltage relation of a capacitor, $Q = CV$, where, Q is the accumulated charge, C is the constant capacitance, and V is the applied voltage. The current is then obtained from Eq. (4) following the product rule of differentiation as:

$$I(t) = \dot{Q}(t) = C(t)\dot{V}(t) + V(t)\dot{C}(t). \quad (5)$$

2.1. Limitation of classical charge-voltage relation

Let there be a capacitor with a time-varying capacitance, $C(t)$, such that,

$$C(t) = C_0 + C_\phi(t), \quad (6)$$

where C_0 is the constant geometric capacitance and $C_\phi(t)$ is the time-varying part of capacitance. The time-varying part of the capacitance is due to the dielectric media present in the capacitor, see Eq. (2) in Ref. [38]. Further, we assume the time-varying part of the capacitance to be a linear function given by, $C_\phi(t) = \phi t$, where the constant, $\phi > 0$. Since capacitances add in parallel circuits, the equivalent circuits are shown in Figs. 1 (a) and (b). On substituting Eq. (6) in Eqs. (4) and (5), we respectively have the following:

$$Q(t) = (C_0 + \phi t)V(t), \text{ and} \quad (7)$$

$$I(t) = C_0\dot{V} + \phi t\dot{V} + V\phi. \quad (8)$$

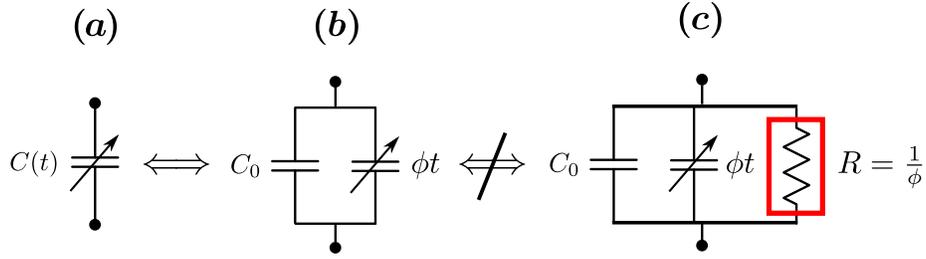


Figure 1: (a) Symbol for a time-varying capacitor with a time-varying capacitance, $C(t)$. (b) The equivalent model of (a), assuming a linearly time-varying capacitance, $C(t) = C_0 + \phi t$. (c) The inequivalent model with an undesired resistor that emerges from the application of the classical relation, $Q(t) = C(t)V(t)$, to (b).

On carefully observing the three additive terms on the right hand side of Eq. (8), we find that the first two corresponds to capacitor currents that flow through the capacitors of capacitances, C_0 and C_ϕ , respectively, but the third term is the Ohmic current that flows through a resistor of equivalent resistance, $1/\phi$. Since currents add in parallel branches, Eq. (8), corresponds to a parallel combination of the three elements as shown in Fig. 1 (c). Clearly, this is not equivalent to the Fig. 1 (b). This anomaly may also be verified as follows. On imposing the initial condition at time, $t = 0$, we have from Eq. (8), the current, $I_0 = C_0\dot{V} + V\phi$, instead of the expected, $I_0 = C_0\dot{V}$. Further, if V is constant, $\dot{V} = 0$, then the current through the capacitor should be null, but Eq. (8) predicts an undesired ohmic current, $V\phi$. The root cause of this problem can be traced back to the classical relation, Eq. (4), which is not valid for a time-varying capacitance [38, 46]. The underlying reason behind the inequivalence of Figs. 1 (b) and 1 (c) is that the traditional charge-voltage relation assumes a linearly time-invariant system, i.e., $Q(t) = f(V(t))$. In contrast, a time-varying capacitance invokes a time-variant system, $Q(t) = f(V(t), t)$, i.e., the capacitor remembers the applied voltage that it was subjected to, in the past [46]. The classical relation leads to a term-by-term multiplication of $C(t)$ and $V(t)$ at any given instant of time, t , and therefore it does not take the capacitor memory into account.

Here it is necessary to emphasize that even though the classical relation is

only applicable for capacitors with a constant capacitance [46], Eqs. (4) and (5) have been widely used by physicists and engineers for describing capacitors with time-varying capacitances. Unfortunately, this has been overlooked in the time-varying circuit theory [63], as well as in the basic circuit theory [67]. Similarly, even the simulation tools such as those from Matlab and Micro-Cap [62] also use Eq. (5) to model current through capacitors with time-varying capacitances.

2.2. Modification of classical-charge voltage relation

The time-varying aspect of the capacitance has already been known to the industrial manufacturers of capacitors but in lack of a better model than that expressed by Eq. (4), they circumvent this lacking by defining capacitance at 1 kHz [38]. Interestingly, a meticulous attempt was made by Westerlund to resolve this problem by proposing a charge-voltage relation for a universal capacitor model [38]. Unfortunately, contrary to the expectation that work did not attracted significant interest among the electrical engineers community because of three reasons. First, the lack of a closed-form expression for the charge-voltage relation, see the abstract and Eqs (16) and (17) in Ref. [38]. Second, though the results were motivated from the experimental observations, the underlying issue with the classical relation was not discussed. It is to be noted that this has now been been addressed in the previous subsection. Third, the acceptability of the fractional derivatives among the scientific community was relatively less three decades ago than it is now [48, 49]. Here we aim to present a closed-form expression for the charge-voltage relation of a universal capacitor model that also addresses the limitations of the classical model.

The memory characteristic of the capacitor is taken into account through the following proposed charge-voltage relation,

$$Q(t) = C(t) * \dot{V}(t), \quad (9)$$

where, “*” represents the convolution operation. Since the system is time-varying, yet linear, the derivative property of the convolution is applicable. Further, substituting Eq. (6) in Eq. (9) and following the derivative property of

the convolution, we obtain the capacitor current as:

$$I(t) = C(t) * \ddot{V}(t) = [C_0 * \ddot{V}(t)] + [\phi t * \ddot{V}(t)]. \quad (10)$$

It is worth noticing that the expressions for, Q and I , in Eqs. (9) and (10), are actually motivated from the fractional derivatives as they provide an appropriate mathematical framework to model memory-driven systems. The expression for the current, Eq. (10), when seen in light of Eq. (2), gives,

$$I(t) = C_0 \dot{V}(t) + \phi V(t). \quad (11)$$

Here, an important observation is that a parallel combination of a constant capacitance capacitor, C_0 , and a time-varying capacitor, C_ϕ , is equivalent to the parallel combination of the constant capacitance capacitor and a resistor whose resistance is given by $1/\phi$. Also, at any instant of time, $V(t) \equiv t \dot{V}(t)$, which when substituted back in Eq. (11), leads to,

$$I(t) = I_{C_0}(t) + I_{C_\phi}(t), \quad (12)$$

where $I_{C_0}(t) = C_0 \dot{V}(t)$, and $I_{C_\phi} = C_\phi \dot{V}(t)$,

are the capacitor currents that flow through the capacitors of capacitances, C_0 and C_ϕ , respectively. It is also possible to obtain Eq. (12) from Eq. (10) using the standard convolution integral, however if the time-varying capacitance is expressed in the form of a power-law, then fractional framework turns out to be a readily available tool for their analysis. The correctness of the Eq. (12) that stems from the modified charge-voltage relation can be confirmed in three independent ways. First, the application of Kirchoff's current law to the parallel combination of the capacitors in Fig. 1 (b) yields the same expression as Eq. (12), which would also be the case if the term, $V(t) \dot{C}(t)$, from Eq. (5), is ignored. It can be concluded that the last term, $V(t) \dot{C}(t)$, in Eq. (5), that leads to the undesired term, $V\dot{\phi}$, in Eq. (8), is not required at all. Fortunately, this has been experimentally verified as well [68]. Second, in contrast to the Eq. (8), Eq. (12) does not contain any undesired ohmic current term and is therefore equivalent to the current flowing in the circuit shown in Fig. 1 (b). Thus the inequivalence

that arose due to the conventional charge-voltage relation, Eq. (4), is resolved through the convolution relation, Eq. (9). Third, on integrating the current expression, Eq. (12), to obtain the respective charge, it naturally leads to the modified charge-voltage relation:

$$Q(t) = \int_0^t (C_0 + \phi\tau) \frac{dV(t-\tau)}{d(t-\tau)} d\tau = C(t) * \dot{V}(t), \quad (13)$$

instead of the classical relation, $Q = CV$.

Further, even though we have assumed a linearly time-varying capacitance, the proof that we have presented here can be generalized to all power-law forms of the time-varying capacitance using fractional derivatives. On replacing, $C(t)$, in Eq. (10) by $C_0(\tau/t)^{\alpha-1}/\Gamma(2-\alpha)$, and then interpreting the resulting equation in light of Eq. (2), we obtain the expression for the current through a fractional capacitor as [69]:

$$I_{C_f}(t) = C_0\tau^{\alpha-1} \left[\frac{t^{1-\alpha}}{\Gamma(2-\alpha)} * \ddot{V}(t) \right] = C_f \frac{d^\alpha}{dt^\alpha} V(t), \quad (14)$$

where, $C_f = C_0\tau^{\alpha-1}$. If the capacitance is assumed to be a constant, i.e., $C_\phi = 0$, then results from Eqs. (9) and (10), reduce to the classical relations, $Q(t) = C_0V(t)$ and $I(t) = C_0\dot{V}(t)$, respectively, which is expected for a time-invariant system. This can be witnessed from Eq. (12) too. The same also mirrors from Eq. (14), for $\alpha = 1$, which corresponds to a memory-less system. Since Eq. (14) is obtained from Eq. (10) which in turn has its origin in the Eq. (9), it is confirmed that Eq. (9) corresponds to the charge-voltage relation for a fractional-capacitor. It is clarified that in contrast to the dimensionally consistent modified charge-voltage relation introduced in this manuscript, other competing expressions are not even dimensionally consistent, example, Eq. (5) from Ref. [69]. It is to be emphasized that the modified charge-voltage relation can already be witnessed in a scattered, non closed-form in Ref.[38]. Since the charge-voltage relation of a fractional capacitor has been quite desired by the fractional calculus community, we regard this as one of the intermediate findings reported in this manuscript. The implications of this relationship can be guessed

from the fact that it is inherently required in the modeling of dielectric media [11, 70–73], supercapacitors [43, 74], and electrochemical capacitors [75].

3. Curie-von Schweidler law from time-varying capacitance

Since the expressions of the Nutting law [45] and the CvS law are quite similar, it is natural to follow the same route to derive the CvS law and so we replace the rheological modeling elements by their respective electrical analogues. We replace the spring, the constant viscosity dashpot, and the time-varying dashpot from the modified Maxwell model of Fig. 1 (a) from Ref. [45], by a resistor of resistance R , a capacitor of constant capacitance, C_0 , and a capacitor of time-varying capacitance, $C_\chi(t)$, respectively. Since individual capacitances add in parallel circuits, the net capacitance, $C(t)$, becomes

$$C(t) = C_0 + C_\chi(t), \quad C_\chi(t) = \theta t, \quad \text{and} \quad \theta = \left. \frac{dC(t)}{dt} \right|_{t=0} > 0, \quad (15)$$

where C_0 is the constant geometric capacitance and $C_\chi(t)$ is the capacitance due to the dielectric material of the capacitor. The circuit model is shown in Figs. 2 (a) and (b), in which R and $C(t)$ may be interpreted as the bulk dielectric and the time-dependent barrier respectively [1]. The assumption of a time-varying capacitance is not *ad hoc*, it manifests from a delayed-response that arises due to a time-dependent charge carrier distribution in dielectrics [76–78]. Interestingly, similar assumptions of time-varying capacitance have been used to harness energy [64] and describe properties of cerebral microvasculature [65].

Let a unit step voltage, V_0 , be applied to the circuit at, $t = 0$, such that I_R , I_C , V_R , and V_C , are the currents and the voltages across the resistor and the capacitor respectively. The voltage, $V_C(t)$, is the same in the parallel branches that has the two capacitors. Since the time-varying capacitance yields a time-variant system, the modified charge-voltage relation from the previous section is used. So, the current through the parallel combinations of the capacitors is, $I_C = I_{C_0} + I_{C_\chi} = C_0\dot{V}_C + \theta t\dot{V}_C$. This expression can also be directly extracted

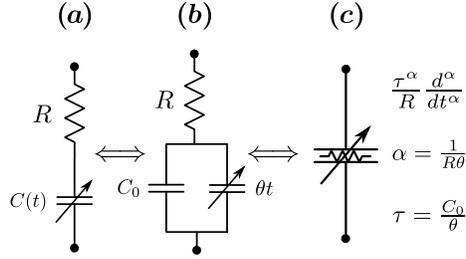


Figure 2: (a) Circuit model consisting of a series combination of a resistor, R , and a time-dependent capacitor, $C(t)$. (b) Equivalent circuit of (a). (c) The proposed new symbol for the fractional capacitor that has a similar current response as (a).

from Eq. (17) of Ref. [38] that also experimentally established the inapplicability of the classical charge-voltage relation for media that exhibit memory [46]. Now we have, $\dot{V}_C = I_C / (C_0 + \theta t)$. In a series arrangement, $I_R = I_C = I$, and $V_0 = V_R + V_C$. Since, $\dot{V}_0 = \dot{V}_R + \dot{V}_C = 0$ and $\dot{V}_R = \dot{I}_R R$, this gives,

$$R\dot{I} + \frac{I}{(C_0 + \theta t)} = 0. \quad (16)$$

The integration then yields,

$$R \ln I = -\frac{\ln(C_0 + \theta t)}{\theta} + \ln K. \quad (17)$$

Further, at $t = 0$, the current flows through the resistance alone, i.e., $I(t = 0) = I_0 = V_0/R$. On imposing this initial condition, the integration constant, $\ln K$, is obtained as, $\ln K = R \ln I_0 + (\ln C_0)/\theta$, which on substituting back into its parent equation gives,

$$I(t) = I_0 \left(1 + \frac{\theta}{C_0} t\right)^{-1/(R\theta)}. \quad (18)$$

If the time-varying part of the capacitance dominates over the constant capacitance, i.e., if $C_\chi(t) = \theta t \gg C_0$, then Eq. (18) is approximated to,

$$I(t) \approx I_0 \left(\frac{\theta}{C_0} t\right)^{-G/\theta}, \quad (19)$$

which is the CvS law. On comparing Eq. (19) with Eqs. (1) and (3), the parameters of the UDR and the fractional capacitor gain physical interpretation

as:

$$a = \frac{V_0}{R}, \quad \alpha = \frac{G}{\theta}, \quad \tau = \frac{C_0}{\theta}, \quad C_f = G \left(\frac{C_0}{\theta} \right)^\alpha, \quad \text{and } G = \frac{1}{R}. \quad (20)$$

Further since the fractional capacitor satisfies the Kramers-Kronig relations [46], this naturally extends to the circuit model shown in Fig. 2 (a). A new symbol for the fractional capacitor is proposed in Fig. 2 (c) to distinguish it from the symbol used in Figs. 2 (a) and (b) that has traditionally been used to represent the varying-capacitance due to the voltage-induced nonlinearity. The new symbol has a resistance symbol sandwiched in between the parallel plates symbol of a capacitor which closely relates to the derivation presented here.

It can be seen from Eqs. (19) and (20) that as $\alpha \rightarrow 0$, $I \rightarrow I_0$, and $C_f \rightarrow 1/R$. This means the dielectric behaves purely resistive in accordance to the Ohm law which can also be verified from Eq. (3). However, as $\alpha \rightarrow 1$, there are two possible outcomes that are dependent on the magnitude of the ratio, t/τ . On the one hand, as $t/\tau \rightarrow \infty$, it implies, $\tau \rightarrow 0$, and so, $\theta \rightarrow \infty$, which in turn yields, $C(t) \rightarrow \infty$. This is in agreement with the observation for polypropylene for which $1 > \alpha > 0.999$ [38]. Further, at such long time scales, $I \rightarrow 0$, and this can be verified from Eq. (19) as well as from Eq. (3), where $C_f \rightarrow 0$. On the other hand, at short time scales, i.e., $\tau/t \rightarrow \infty$, Bernoulli's expression for the exponential is used in Eq. (18) to yield an exponential decaying current, $I \rightarrow I_0 \exp(-t/\tau)$. This memory-less current from an ideal capacitor is expected because such short time scales necessitates, $\theta \rightarrow 0$. Alternatively, there is no significant contribution to the capacitance from its time-varying part, $C_\chi(t)$, at short-time scales. This implies that the circuit model from the Fig. 2 (b) is reduced to the series combination of R and C_0 , which is the equivalent circuit for the Debye response. This is also verifiable, since as, $\alpha = 1/R\theta \rightarrow 1$, $\theta \rightarrow 1/R$, which leads to, $\tau = C_0/\theta \rightarrow RC_0 = \tau_D$, where τ_D is the Debye relaxation time constant. Therefore, it is inferred that a non-Debye dielectric media appears as a Debye media at very short time scales. To summarize, the case, $\alpha \rightarrow 1$, hints at the presence two different relaxations time constants, $\tau_D = RC_0$, at short times, and $\tau = C_0/\theta$, at long times. It is therefore inferred that the

Debye relaxation mechanism and the non-Debye relaxation mechanism are two independent mechanisms that coexist and occur sequentially in a dielectric. This is in accordance with the experimental observations [1, 9, 19, 20], which may also explain the sensitivity of the curve-fitting parameters to the frequency window employed in the analysis [79]. The transition from the Debye relaxation to the non-Debye relaxation is termed as the “*regenerated memory effect*”, and has already been experimentally observed, see Figs. [4] and [5] in Ref. [16]. In the frequency domain, the high-frequency dispersion due to the Debye response may be seen as a natural extension of the low frequency dispersion due to the UDR. This is in agreement with the published reports [9, 16, 19, 39]. Since the revelation of the hidden Debye response came from the UDR expressed by Eq. (18), it should rather be preferred over its approximated version, Eq. (19).

Experimental data					Theoretical predictions from Eq.(20)	
Source	C_0	R	τ	α	$\theta = C_0/\tau$	$\alpha = 1/(R\theta)$
Ref. [46, Fig. 5]	1 μF	1 $\text{M}\Omega$	1 s	0.982	1 $\mu\text{F}/\text{s}$	1
Ref. [16, Fig. 5]	2 μF	200 $\text{k}\Omega$	0.4 s	0.998	5.01 $\mu\text{F}/\text{s}$	0.998

Table 1: Comparison of the experimental data against the theoretical predictions from Eq.(20).

In order to further consolidate the findings, reported results are compared with the experimental data in Table 1. The charging of a capacitor consisting of metalized paper was investigated in Ref. [46], in contrast, the charging of a capacitor consisting of oil-impregnated technical paper was studied in Ref. [16]. A reasonably good agreement between the experimental observations and the predictions from Eq.(20) can be witnessed for the value of the power-law exponent, α . In fact, the predicted value of the current, $a = V_0/R = 10^{-3}$ A, is almost identical to the observed value, see Ref. [16, Fig. 5], where the applied voltage bias, $V_0 = 200\text{V}$, was used.

4. Discussion

We have achieved three goals here. *First*, the time-honored UDR is identified as an electrical analogue of Nutting's law. The derivation and the subsequent analysis presented here is in accordance to Jonscher's prediction of a satisfactory theory that is almost independent of the detailed physical and chemical nature of the dielectrics. Moreover, given the overwhelming applicability of the UDR, it was quite likely that a fundamental unifying principle was found based on a simple assumption. The fact that both Nutting's law and CvS' law have been derived in the framework of fractional calculus from the simple assumptions of a time-varying viscosity and a time-varying capacitance respectively may also be favored by the law of parsimony. This asserts the effectiveness of fractional derivatives in modeling of materials that exhibit memory.

Second, the parameters of the UDR have gained physical interpretation and therefore they may reduce ambiguities in the curve-fitting. Since the fractional capacitor has its origin in the UDR, the benefits automatically extend to those circuit models that have fractional derivatives in them [80].

Third, it is shown that a time-varying capacitor is governed by the equation, $Q(t) = C(t) * \dot{V}(t)$, that has also led to experimentally verifiable results. The convolution relation also reduces to the classical relation, $Q(t) = CV(t)$, if the capacitance is assumed to be a constant. Therefore, we believe the former should be preferred over the latter as that is applicable for both memory-less as well as memory-laden media. The convolution relations should be seen as relations that complete the bigger picture and yet retain the beauty of the classical relations. Moreover, since the fractional capacitor is also considered as the *universal capacitor*, the relation, $Q(t) = C(t) * \dot{V}(t)$, may be regarded as the *universal* charge-voltage relation for capacitors. It is expected that this finding may further boost the emerging field of fractional-order circuits and systems.

Although phenomenological models have been used here, it is shown that a careful analysis of them could facilitate a cross-fertilization of the disparate fields of non-Newtonian rheology and dielectric spectroscopy in the framework

of fractional calculus. The preference for the fractional derivatives in describing complex media that exhibit memory is similar in principle to the preference given to an appropriate coordinate system that suits the geometry of the physical phenomena under investigation. We note that fractional calculus is not just a mathematical tool that can only be used to curve-fit the anomalous behavior of complex media. Rather, it has an inherent connection with physics too that needs to be explored more.

Lastly, we accept a probable critique of this work, which is, that the model presented here is macroscopic and is probably not reducible to a microscopic level. Even though the underlying reason for that has already been discussed before in Sec. 1, we would like to stress upon the idea that the arising of memory in a material may be regarded as an example of *weak emergence*. This is actually in accordance to the finding that even if a perfect, complete description of the microscopic interactions between a material's particle is available, it may not always be sufficient to deduce its macroscopic properties [81]. The idea of emergence should not be seen here as an excuse for the lack of knowledge, rather we are optimistic and confident about the explanatory powers of science. A similar yet a contrasting notion is that if a macroscopic model can describe an experimentally established physical law, then probably the difference between a macroscopic and a microscopic description is merely an ideological one.

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